

Sub
P
a semiconductor layer having a number of layers of 1 or more formed on the light-emitting layer, and wherein a top surface of the semiconductor layer is roughened so as to define a roughened surface.

16. (New) The semiconductor light-emitting device according to claim 15, wherein the light-emitting layer is a single layer or a plurality of layers comprising $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

17. (New) The semiconductor light-emitting device according to claim 15, wherein the semiconductor layer whose top surface is a roughened surface comprises $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$).

18. (New) The semiconductor light-emitting device according to Claim 17, wherein the semiconductor layer comprising $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$) is transparent to an emission wavelength.

REMARKS

This is in response to the Office Action dated October 2, 2002. Non-elected claims 9-14 have been canceled, without prejudice in view of the Restriction Requirement. New claims 15-18 have been added. Thus, claims 1-8 and 15-18 are now pending.